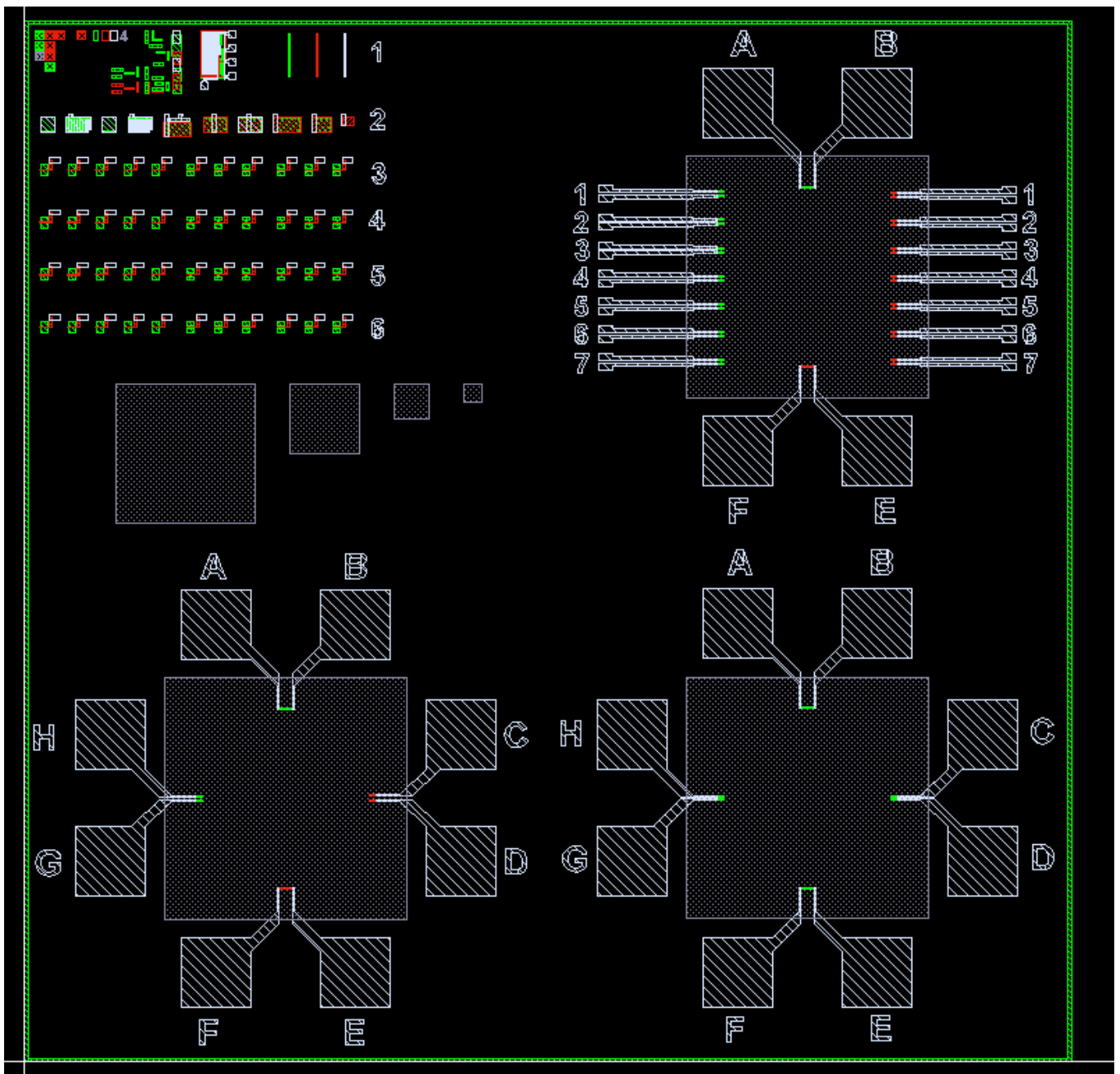
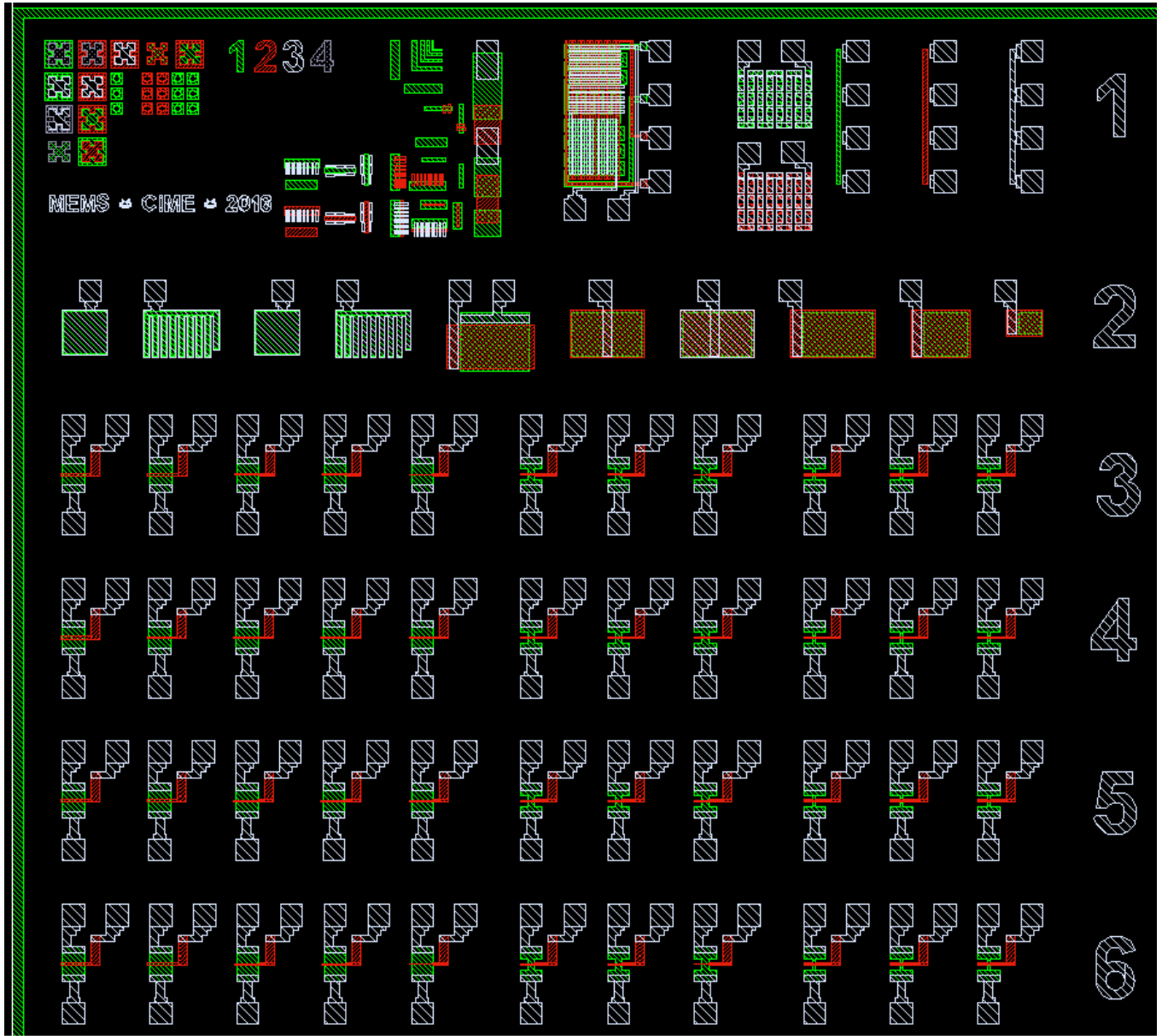


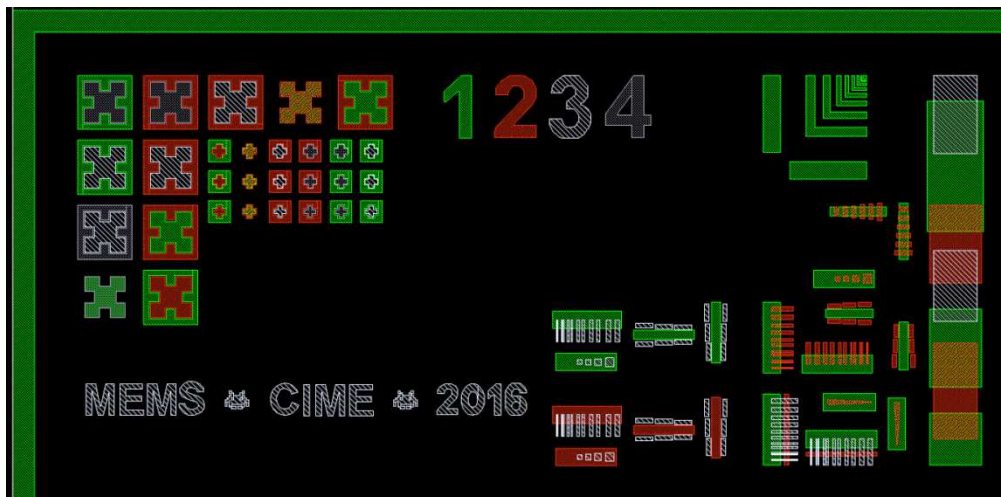
Réticule :



Lignes 1 à 6 :



Ligne 1 : motifs d'alignement

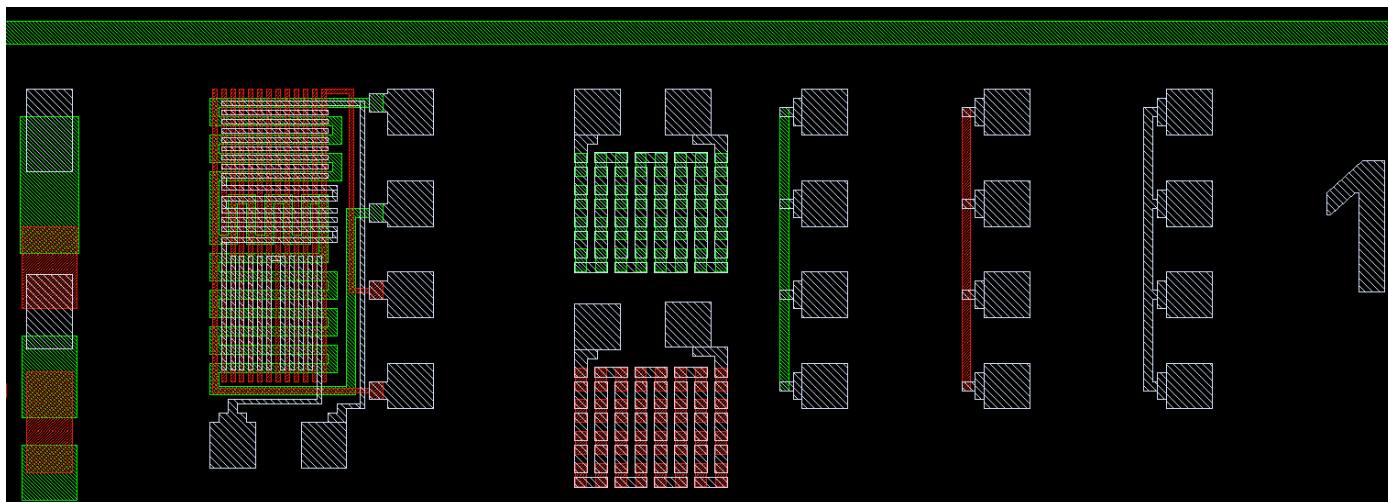


Niveau 1 : DIFF

Niveau 2 : POLY

Niveau 3 : METAL

Niveau 4 : FAR

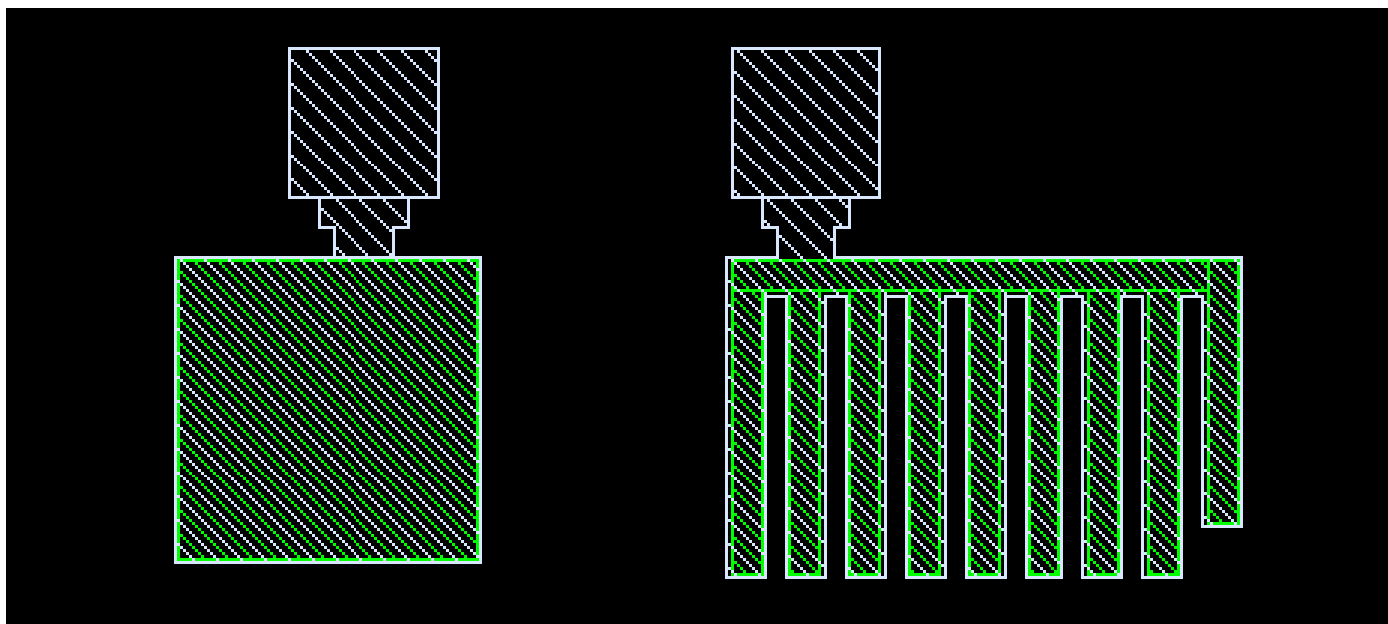
Ligne 1 :

Motif test profilomètre, 2 chaînes de contacts, et barreaux R carrée métal, poly et cristal Silicium dopé
 $600\mu\text{m} * 20\mu\text{m}$ soit 30 carrés; Taille des plots de métal : $1000\mu\text{m} * 1000\mu\text{m}$;
 Numéros des niveaux de masque : 1 DIFFusion, 2 POLY(Silicium xCristallin), 3 METal (Aluminium), 4 gravure Face
 ARrière

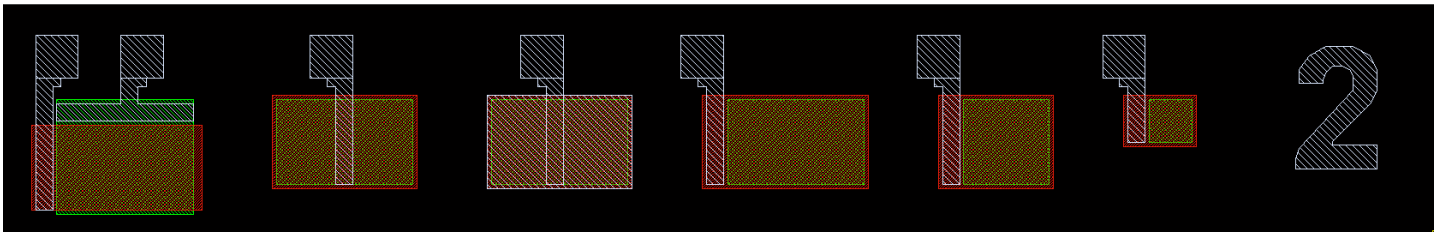
Ligne 2:

Diode $200 * 200\mu\text{m}$ de grande surface et petit périmètre ;

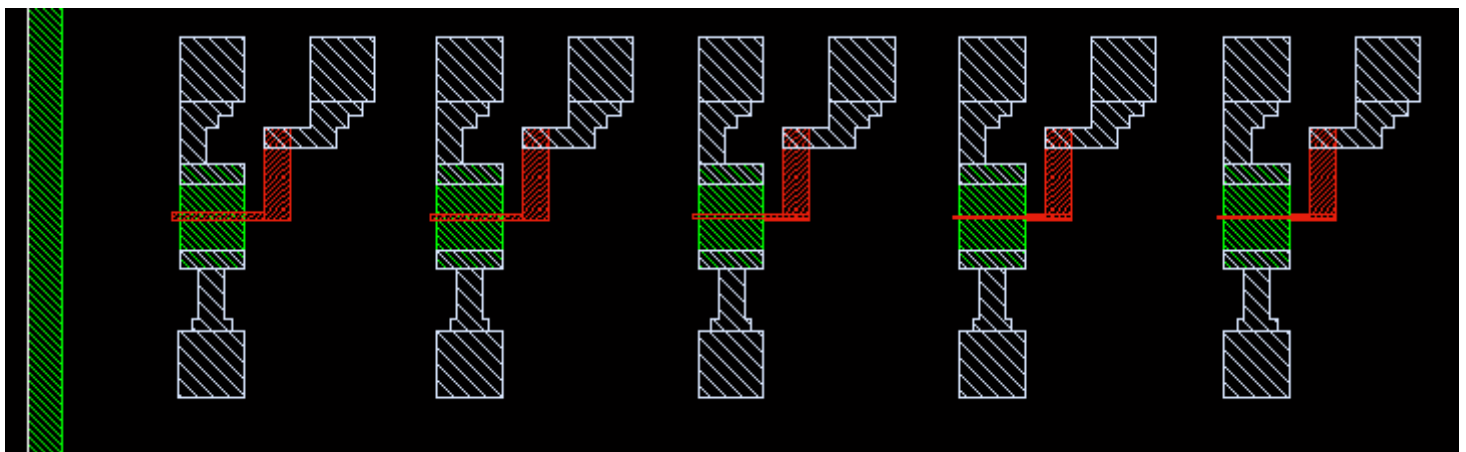
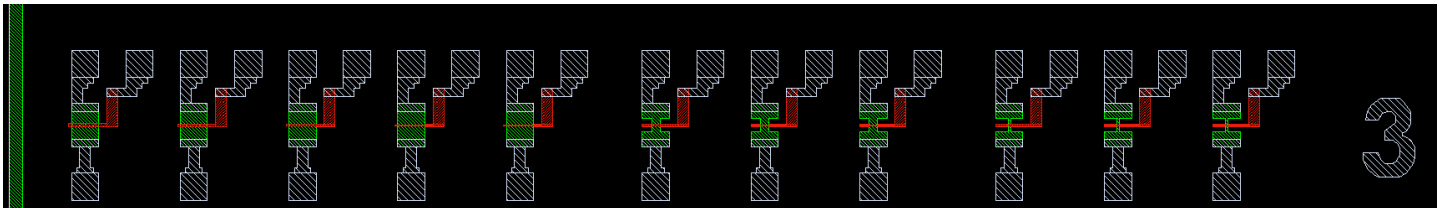
diode de grande surface et de grand périmètre :
 $320\mu\text{m} * 20\mu\text{m}$; $8 * 190\mu\text{m} * 20\mu\text{m}$; $20\mu\text{m} * 76\mu\text{m}$



Capacités MOS (300*200µm, 200*200µm et 100*100µm)

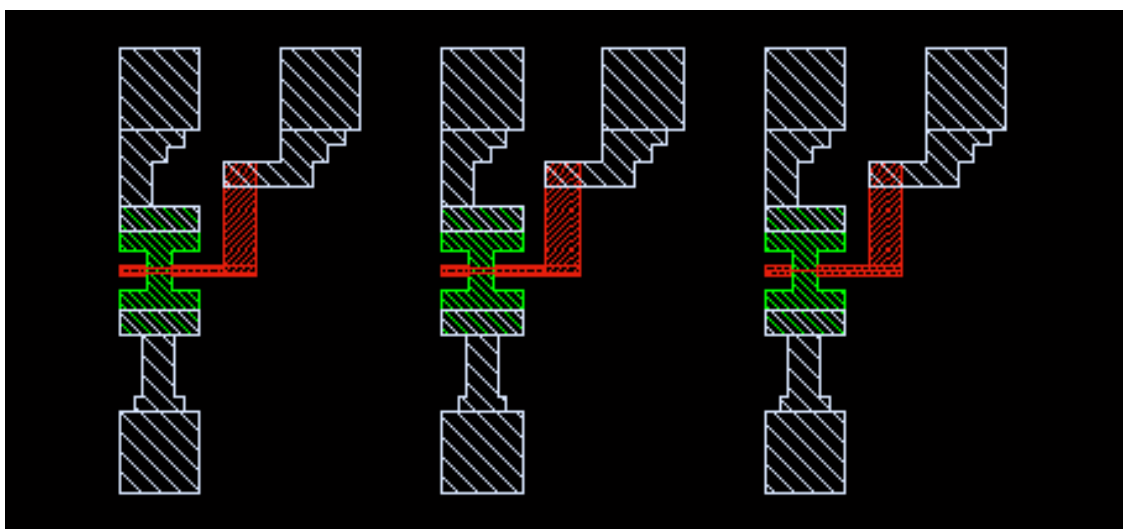


Ligne 3 (4, 5 et 6 identiques) :



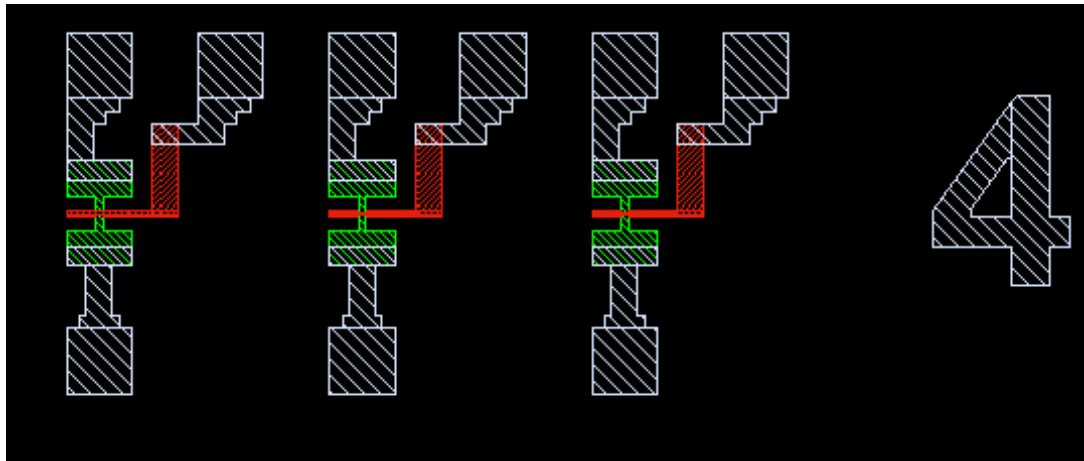
Transistors MOS

W=100µm, l= 12; 10; 6; 4; 2µm



Transistors MOS

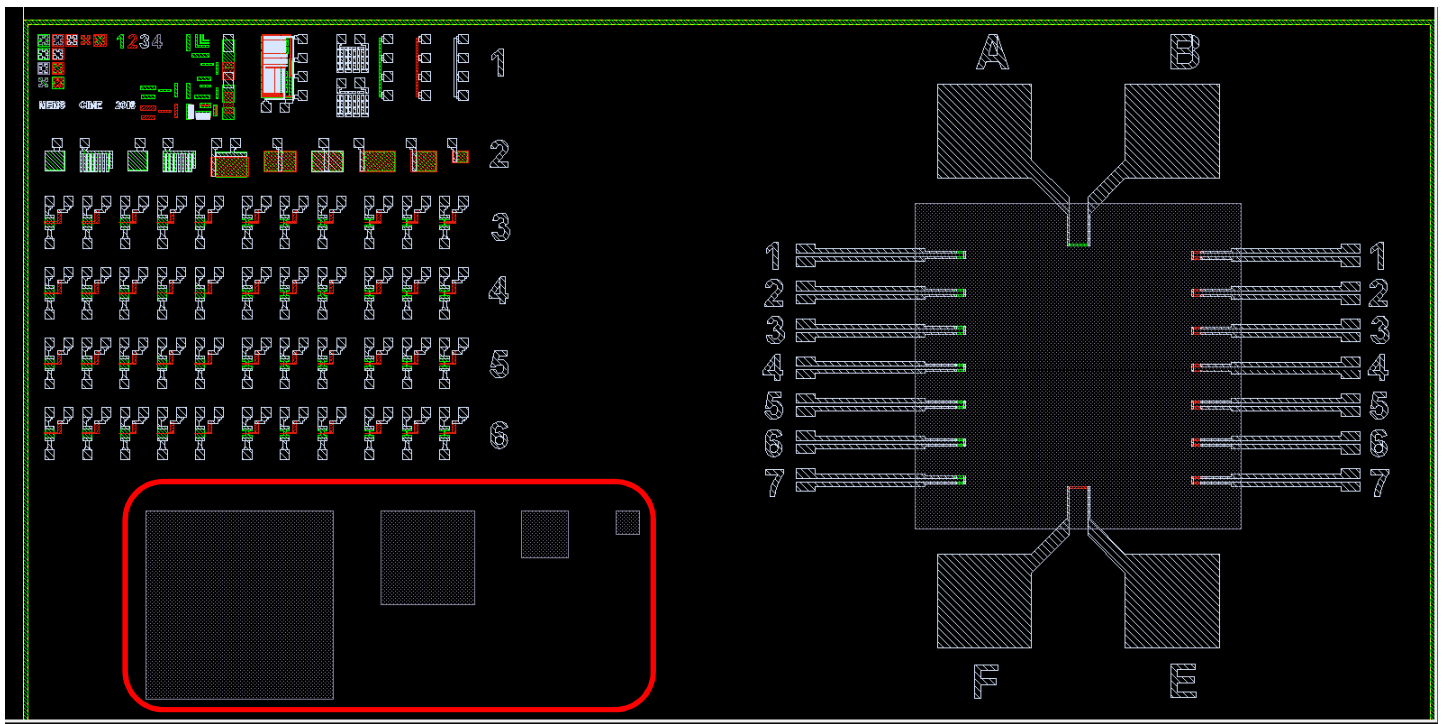
W=30µm, l=8; 4; 2µm



Transistor MOS

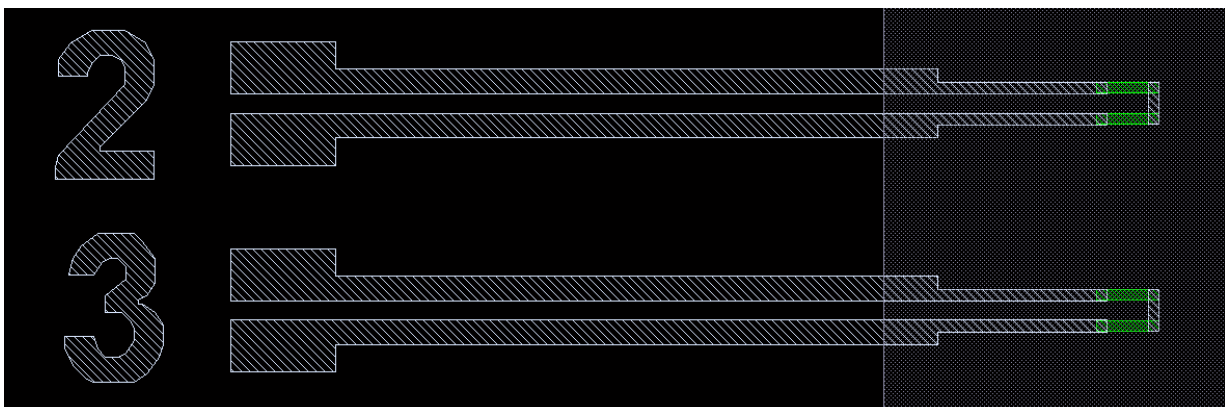
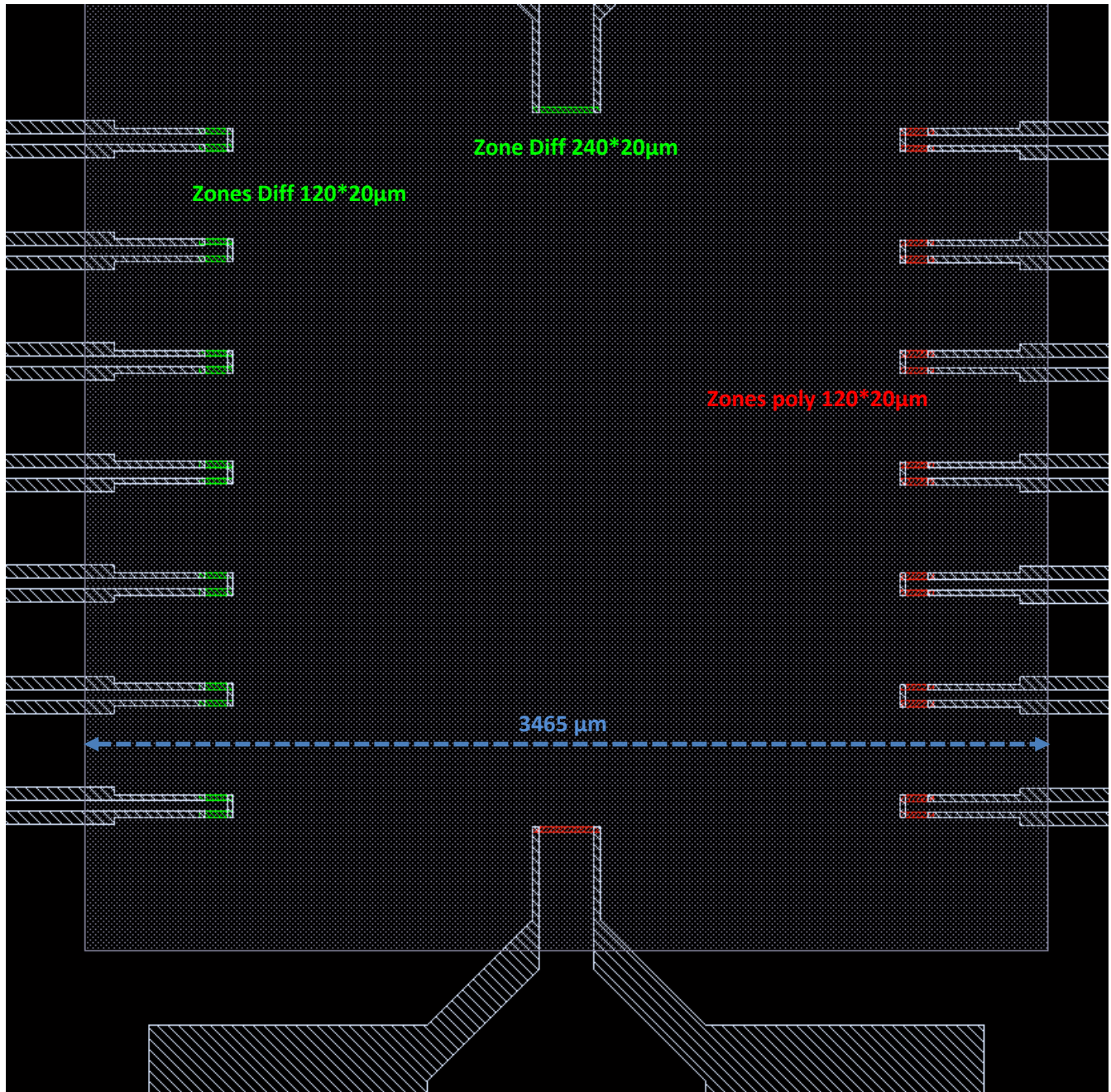
W=10 μ m, l=6; 4; 2 μ m

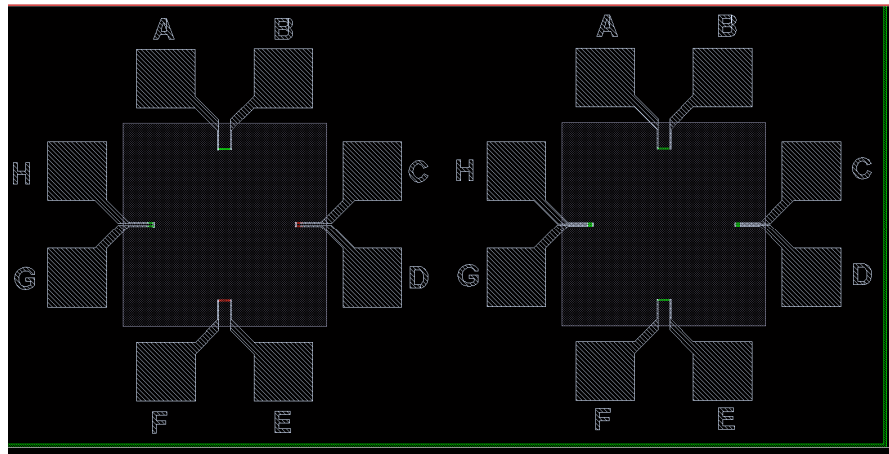
Membranes :



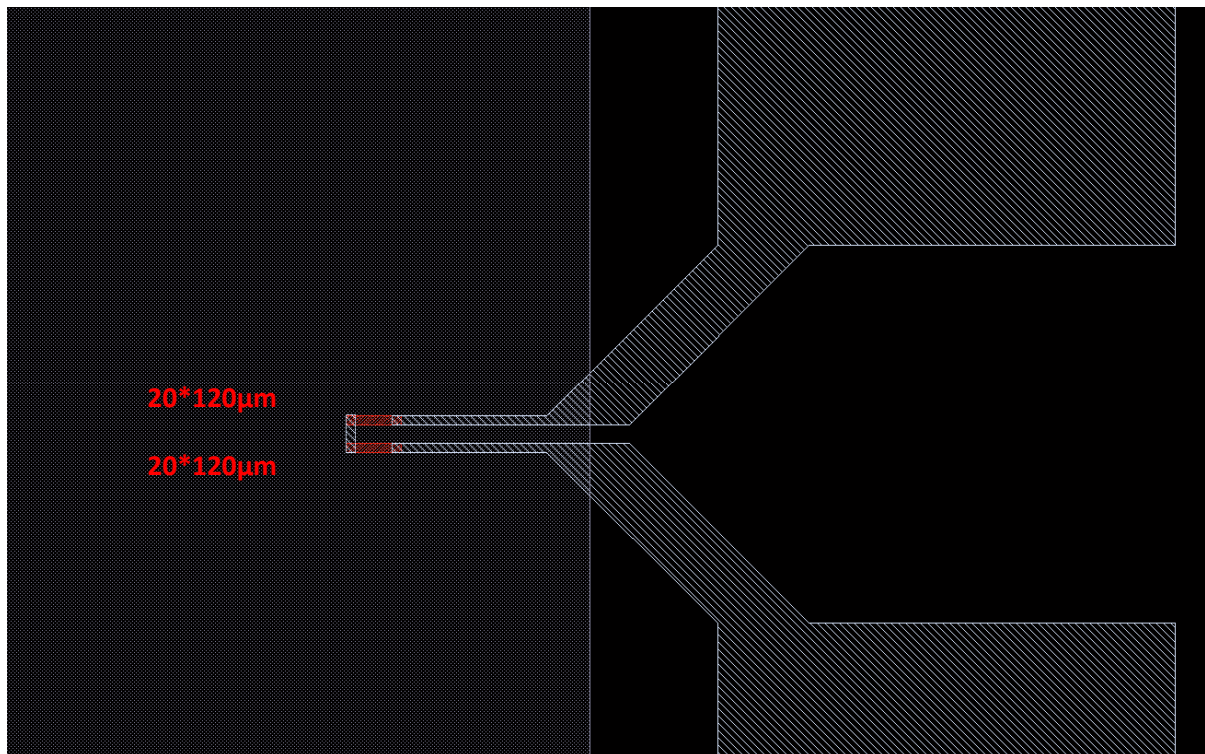
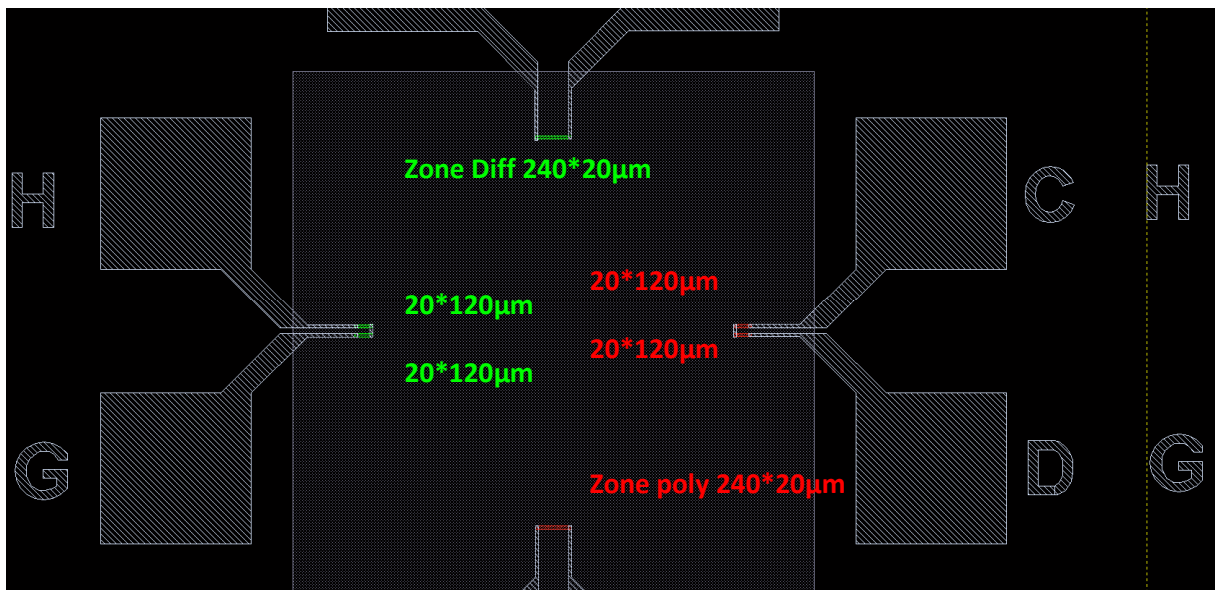
Membranes 2000*2000 μ m; 1000*1000 μ m; 500*500 μ m; 250*250 μ m

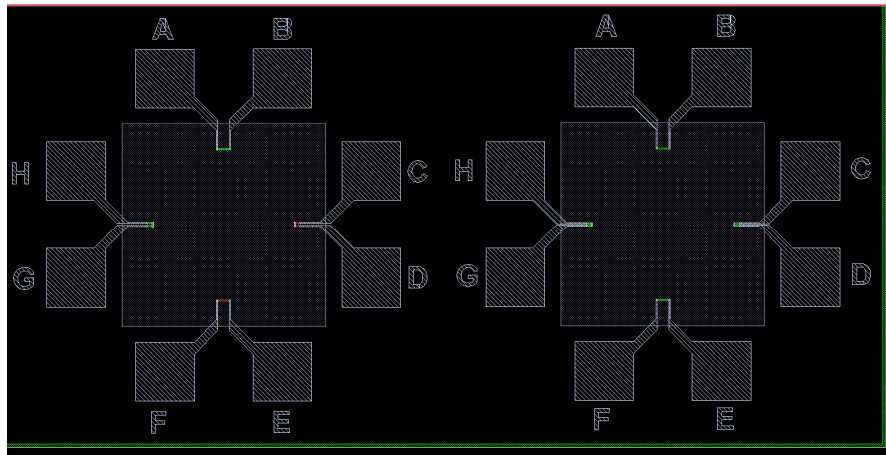
Jauges sur membrane carrée de 3465*3465 μ m





Membrane de gauche :





Membrane de droite:

